

TSM180P03CS

30V P-Channel Power MOSFET



Pin Definition:

- | | |
|-----------|----------|
| 1. Source | 8. Drain |
| 2. Source | 7. Drain |
| 3. Source | 6. Drain |
| 4. Gate | 5. Drain |

Key Parameter Performance

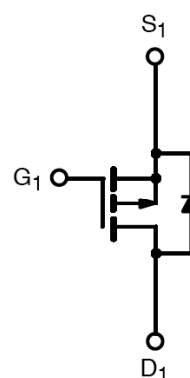
Parameter	Value	Unit
V_{DS}	-30	V
$R_{DS(on)}$ (max)	$V_{GS} = -10V$	18
	$V_{GS} = -4.5V$	30
Q_g	14.6	nC

Ordering Information

Part No.	Package	Packing
TSM180P03CS RLG	SOP-8	2.5kpcs / 13" Reel

Note: "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

Block Diagram



P-Channel MOSFET

Absolute Maximum Ratings ($T_C=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_C=25^{\circ}C$	-10
		$T_C=100^{\circ}C$	-6.3
Pulsed Drain Current (Note 1)	I_{DM}	-40	A
Power Dissipation @ $T_C = 25^{\circ}C$	P_D	2.5	W
Operating Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature Range	T_{STG}	-55 to +150	$^{\circ}C$

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Ambient	$R_{\theta JA}$	50	$^{\circ}C/W$

Electrical Specifications (T_J=25°C unless otherwise noted)

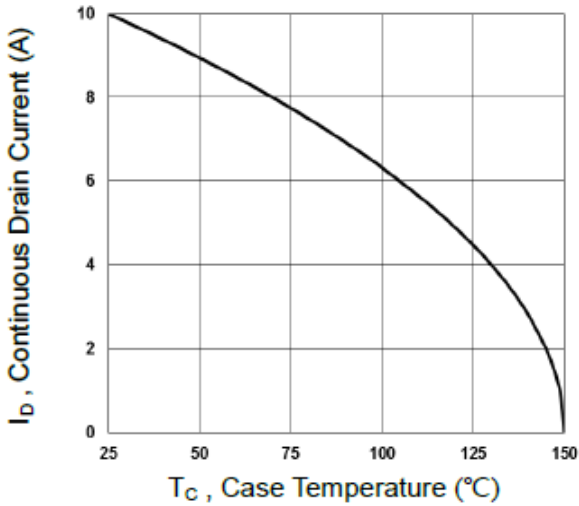
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = -250μA	BV _{DSS}	-30	--	--	V
Drain-Source On-State Resistance	V _{GS} = -10V, I _D = -8A	R _{DS(ON)}	--	14	18	mΩ
	V _{GS} = -4.5V, I _D = -6A		--	23	30	
Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	V _{GS(TH)}	-1.2	-1.6	-2.5	V
Zero Gate Voltage Drain Current	V _{DS} = -30V, V _{GS} = 0V	I _{DSS}	--	--	-1	μA
	V _{DS} = -24V, T _J = 125°C		--	--	-10	
Gate Body Leakage	V _{GS} = ±20V, V _{DS} = 0V	I _{GSS}	--	--	±100	nA
Forward Transconductance ^(Note 2)	V _{DS} = -10V, I _D = -8A	g _{fs}	--	10.5	--	S
Dynamic						
Total Gate Charge ^(Note 2,3)	V _{DS} = -15V, I _D = -8A, V _{GS} = -4.5V	Q _g	--	14.6	--	nC
Gate-Source Charge ^(Note 2,3)		Q _{gs}	--	4.1	--	
Gate-Drain Charge ^(Note 2,3)		Q _{gd}	--	6.3	--	
Input Capacitance	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz	C _{iss}	--	1730	--	pF
Output Capacitance		C _{oss}	--	180	--	
Reverse Transfer Capacitance		C _{rss}	--	125	--	
Switching						
Turn-On Delay Time ^(Note 2,3)	V _{DD} = -15V, I _D = -1A, V _{GS} = -10V, R _{GEN} = 6Ω	t _{d(on)}	--	9	--	ns
Turn-On Rise Time ^(Note 2,3)		t _r	--	21.8	--	
Turn-Off Delay Time ^(Note 2,3)		t _{d(off)}	--	59.8	--	
Turn-Off Fall Time ^(Note 2,3)		t _f	--	14.4	--	
Source-Drain Diode Ratings and Characteristic						
Maximum Continuous Drain-Source Diode Forward Current	Integral reverse diode in the MOSFET	I _S	--	--	-10	A
Maximum Pulse Drain-Source Diode Forward Current		I _{SM}	--	--	-40	A
Diode-Source Forward Voltage	V _{GS} = 0V, I _S = -1A	V _{SD}	--	--	-1	V

Note:

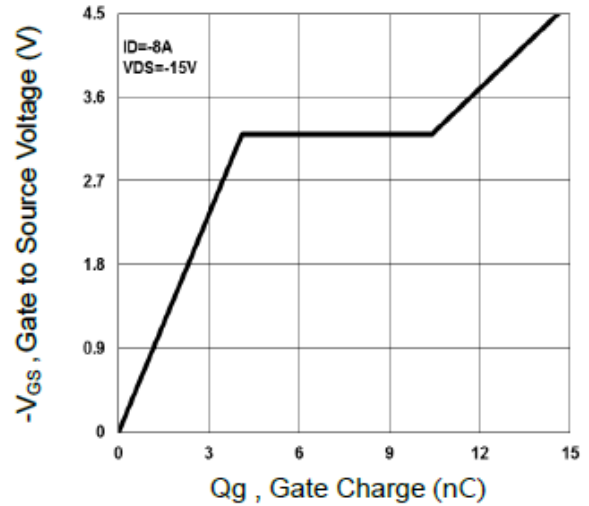
1. Pulse width limited by safe operating area
2. Pulse test: pulse width ≤300μs, duty cycle ≤2%
3. Switching time is essentially independent of operating temperature.

Electrical Characteristics Curve

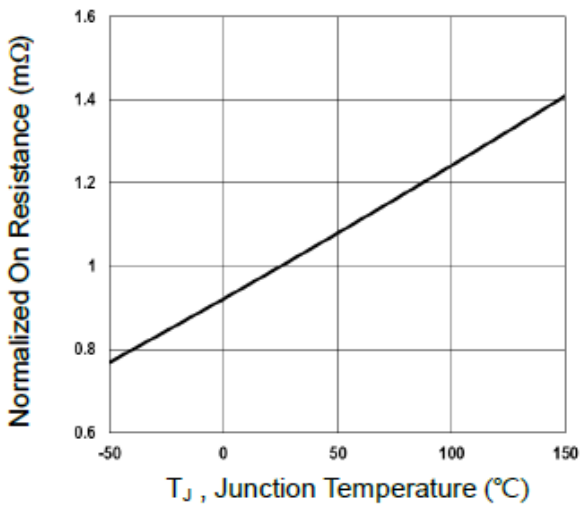
Continuous Drain Current vs. T_C



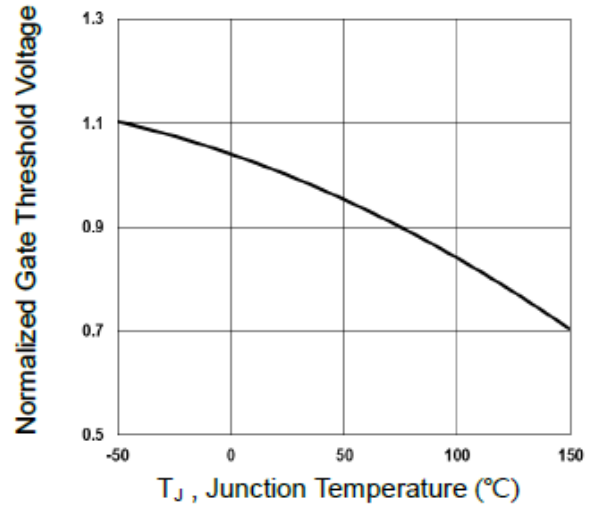
Gate Charge



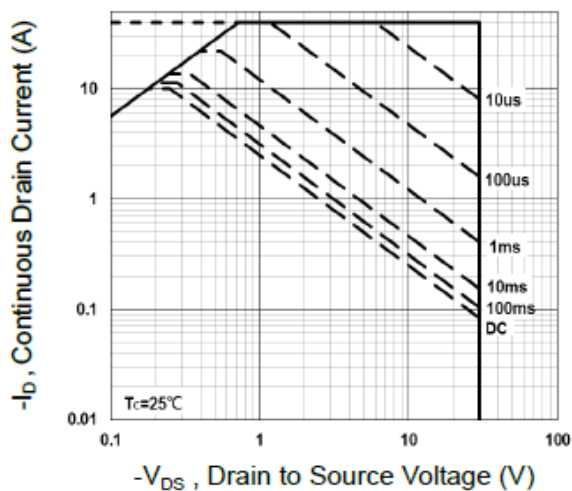
On-Resistance vs. Junction Temperature



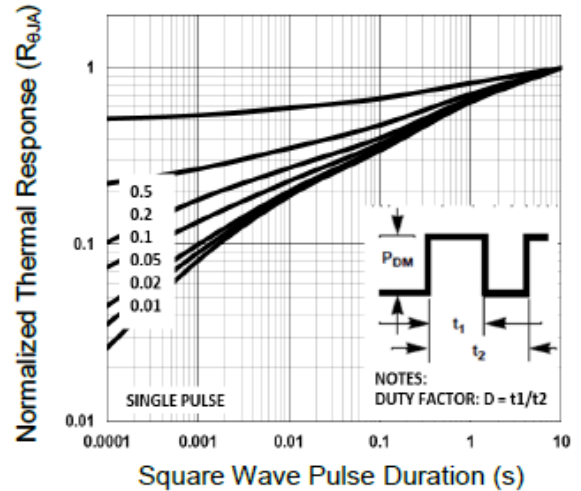
Threshold Voltage vs. Junction Temperature



Maximum Safe Operating Area

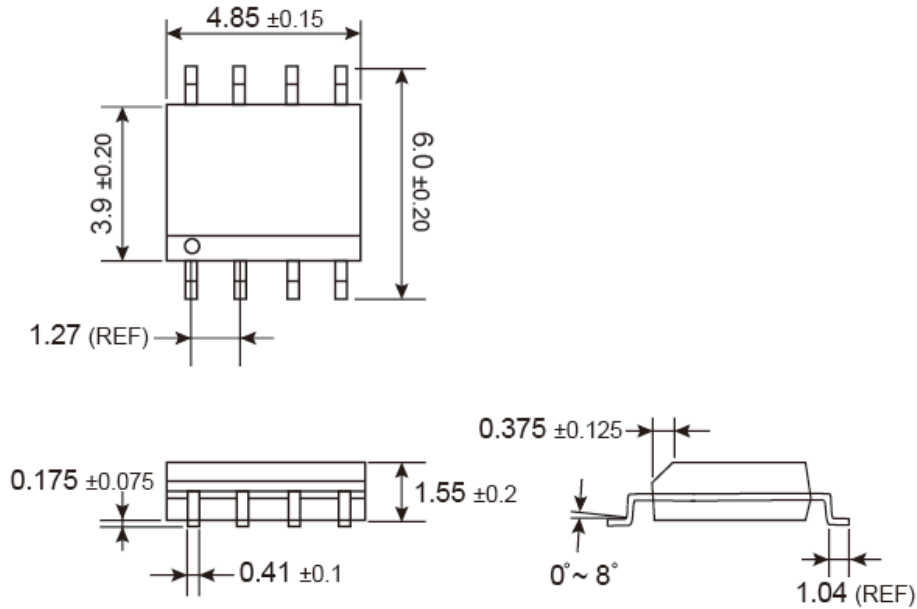


Normalized Thermal Transient Impedance Curve



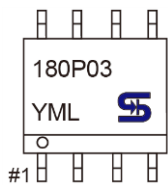


SOP-8 Mechanical Drawing



Unit: Millimeters

Marking Diagram



- Y** = Year Code
- M** = Month Code for Halogen Free Product
 (O=Jan, P=Feb, Q=Mar, R=Apr, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)
- L** = Lot Code

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